

## Amendments to the Specification:

*On page 1, insert the following below the title:*

### CROSS-REFERENCE TO RELATED APPLICATIONS

This application is the U.S. national phase of PCT application number PCT/EP2003/014010, filed September 18, 2003 and published in English under PCT Article 21(2), which further claims the benefit of Singapore patent application serial number 200205833-7 filed September 25, 2002. The entire disclosures of each of these applications are hereby incorporated by reference.

### BACKGROUND OF THE INVENTION

#### 1. Field of the Invention

*Please insert the following subheading prior to the paragraph beginning on page 1, l. 6, as shown below:*

#### 2. Background Art

*Please insert the following subheading prior to the paragraph beginning on page 2, l. 1, as shown below:*

### SUMMARY OF THE INVENTION

*Please insert the following subheading prior to the paragraph beginning on page 3, l. 1, as shown below:*

### BRIEF DESCRIPTION OF THE DRAWINGS

*Please insert the following subheading prior to the paragraph beginning on page 3, l. 10, as shown below:*

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT(S)

*Please amend the paragraph (section) beginning on page 13, at line 15 as shown below:*

The thickness of the low stress LTO layer and the high stress LTO layer is preferably between ~~1000 Å and 10000 Å~~ 1000 Å and 10000 Å.

*Please amend the paragraph (section) beginning on page 14, at line 24 as shown below:*

The thickness of the low stress LTO layer and the high stress LTO layer of the nn+ silicon epitaxial wafer is preferably between ~~1000 Å and 10000 Å~~ 1000 Å and 10000 Å.